# Xin Rong

## List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/5622969/publications.pdf

Version: 2024-02-01

| 46 | 1,056 | 471061 | 414034 |
|---|---|---|---|
| papers | citations | 17 | 32 |
| | | h-index | g-index |

| 46 | 46 | 46 | 1880 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Measuring the Refractive Index of Highly Crystalline Monolayer MoS2 with High Confidence. Scientific Reports, 2015, 5, 8440. | 1.6 | 146 |
| 2 | Tailoring MoS<sub>2</sub> Valleyâ€Polarized Photoluminescence with Super Chiral Nearâ€Field. Advanced Materials, 2018, 30, e1801908. | 11.1 | 99 |
| 3 | Highâ€Outputâ€Power Ultraviolet Light Source from Quasiâ€2D GaN Quantum Structure. Advanced Materials, 2016, 28, 7978-7983. | 11.1 | 72 |
| 4 | Secâ€Eliminating the SARSâ€CoVâ€2 by AlGaN Based High Power Deep Ultraviolet Light Source. Advanced Functional Materials, 2021, 31, 2008452. | 7.8 | 67 |
| 5 | Efficient silicon quantum dots light emitting diodes with an inverted device structure. Journal of Materials Chemistry C, 2016, 4, 673-677. | 2.7 | 64 |
| 6 | Deep Ultraviolet Light Source from Ultrathin GaN/AlN MQW Structures with Output Power Over 2 Watt. Advanced Optical Materials, 2019, 7, 1801763. | 3.6 | 43 |
| 7 | Grapheneâ€Assisted Epitaxy of Nitrogen Lattice Polarity GaN Films on Nonâ€Polar Sapphire Substrates for Green Light Emitting Diodes. Advanced Functional Materials, 2020, 30, 2001283. | 7.8 | 41 |
| 8 | Lattice-Polarity-Driven Epitaxy of Hexagonal Semiconductor Nanowires. Nano Letters, 2016, 16, 1328-1334. | 4.5 | 35 |
| 9 | Deepâ€Ultraviolet Microâ€LEDs Exhibiting High Output Power and High Modulation Bandwidth Simultaneously. Advanced Materials, 2022, 34, e2109765. | 11.1 | 33 |
| 10 | Residual stress in AlN films grown on sapphire substrates by molecular beam epitaxy. Superlattices and Microstructures, 2016, 93, 27-31. | 1.4 | 32 |
| 11 | Repeatable Room Temperature Negative Differential Resistance in AlN/GaN Resonant Tunneling Diodes Grown on Sapphire. Advanced Electronic Materials, 2019, 5, 1800651. | 2.6 | 32 |
| 12 | Generation of Rashba Spinâ€“Orbit Coupling in CdSe Nanowire by Ionic Liquid Gate. Nano Letters, 2015, 15, 1152-1157. | 4.5 | 31 |
| 13 | Hexagonal BNâ€Assisted Epitaxy of Strain Released GaN Films for True Green Lightâ€Emitting Diodes. Advanced Science, 2020, 7, 2000917. | 5.6 | 28 |
| 14 | Identifying a doping type of semiconductor nanowires by photoassisted kelvin probe force microscopy as exemplified for GaN nanowires. Optical Materials Express, 2017, 7, 904. | 1.6 | 24 |
| 15 | High-electron-mobility InN epilayers grown on silicon substrate. Applied Physics Letters, 2018, 112, . | 1.5 | 22 |
| 16 | Experimental Evidence of Large Bandgap Energy in Atomically Thin AlN. Advanced Functional Materials, 2019, 29, 1902608. | 7.8 | 21 |
| 17 | Lattice Polarity Manipulation of Quasiâ€vdW Epitaxial GaN Films on Graphene Through Interface Atomic Configuration. Advanced Materials, 2022, 34, e2106814. | 11.1 | 19 |
| 18 | Multi-bands photoconductive response in AlGaN/GaN multiple quantum wells. Applied Physics Letters, 2014, 104, 172108. | 1.5 | 18 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | Positive temperature coefficient of photovoltaic efficiency in solar cells based on InGaN/GaN MQWs. Applied Physics Letters, 2016, 109, . | 1.5 | 17 |
| 20 | Latticeâ€Symmetryâ€Driven Epitaxy of Hierarchical GaN Nanotripods. Advanced Functional Materials, 2017, 27, 1604854. | 7.8 | 17 |
| 21 | Repeatable asymmetric resonant tunneling in AlGaN/GaN double barrier structures grown on sapphire. Applied Physics Letters, 2019, 114, . | 1.5 | 17 |
| 22 | Lightâ€Controlled Nearâ€Field Energy Transfer in Plasmonic Metasurface Coupled MoS 2 Monolayer. Small, 2020, 16, 2003539. | 5.2 | 16 |
| 23 | Thermally annealed wafer-scale h-BN films grown on sapphire substrate by molecular beam epitaxy. Applied Physics Letters, 2020, 116, . | 1.5 | 16 |
| 24 | Molecular beam epitaxy of single-crystalline aluminum film for low threshold ultraviolet plasmonic nanolasers. Applied Physics Letters, 2018, 112, . | 1.5 | 15 |
| 25 | Role of an ultra-thin AlN/GaN superlattice interlayer on the strain engineering of GaN films grown on Si(110) and Si(111) substrates by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2013, 103, 231908. | 1.5 | 14 |
| 26 | Exciton emission of quasi-2D InGaN in GaN matrix grown by molecular beam epitaxy. Scientific Reports, 2017, 7, 46420. | 1.6 | 14 |
| 27 | Effect of polarization on intersubband transition in AlGaN/GaN multiple quantum wells. Applied Physics Letters, 2013, 102, . | 1.5 | 13 |
| 28 | Intersubband Transition in GaN/InGaN Multiple Quantum Wells. Scientific Reports, 2015, 5, 11485. | 1.6 | 13 |
| 29 | Controlling Phaseâ€Coherent Electron Transport in IIIâ€Nitrides: Toward Room Temperature Negative Differential Resistance in AlGaN/GaN Double Barrier Structures. Advanced Functional Materials, 2021, 31, 2007216. | 7.8 | 12 |
| 30 | Mid-infrared Photoconductive Response in AlGaN/GaN Step Quantum Wells. Scientific Reports, 2015, 5, 14386. | 1.6 | 10 |
| 31 | Effect of indium droplets on growth of InGaN film by molecular beam epitaxy. Superlattices and Microstructures, 2018, 113, 650-656. | 1.4 | 10 |
| 32 | Photoluminescence enhancement of MoS<sub>2</sub>/CdSe quantum rod heterostructures induced by energy transfer and excitonâ€“exciton annihilation suppression. Nanoscale Horizons, 2020, 5, 971-977. | 4.1 | 8 |
| 33 | Individually resolved luminescence from closely stacked GaN/AlN quantum wells. Photonics Research, 2020, 8, 610. | 3.4 | 8 |
| 34 | Photoconductivity in In_xGa_1-xN epilayers. Optical Materials Express, 2016, 6, 815. | 1.6 | 7 |
| 35 | Effect of unintentional nitrogen incorporation on n-type doping of Î²-Ga<sub>2</sub>O<sub>3</sub>grown by molecular beam epitaxy. CrystEngComm, 2022, 24, 269-274. | 1.3 | 6 |
| 36 | Improvement of p -type conductivity in Al-rich AlGaN substituted by Mg Ga Î´ -doping (AlN) m /(GaN) n ( m) Tj ETQq0 0 0 rgBT /Overlock | 2.8 | 5 |

| # | Article | IF | Citations |
|---|---|---|---|
| 37 | Highâ€Efficiency Eâ€Beam Pumped Deepâ€Ultraviolet Surface Emitter Based on AlGaN Ultraâ€Thin Staggered Quantum Wells. Advanced Optical Materials, 2022, 10, . | 3.6 | 5 |
| 38 | Nanoscale visualization of electronic properties of AlxGa1-xN/AlyGa1-yN multiple quantum-well heterostructure by spreading resistance microscopy. Journal of Applied Physics, 2017, 121, 014305. | 1.1 | 4 |
| 39 | Enhanced Hydrogen Detection Based on Mg-Doped InN Epilayer. Sensors, 2018, 18, 2065. | 2.1 | 1 |
| 40 | Impact of Quantum Dots on III-Nitride Lasers: A Theoretical Calculation on Linewidth Enhancement Factors. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-7. | 1.9 | 1 |
| 41 | Growth of a-Plane InN Film and Its THz Emission. Chinese Physics Letters, 2014, 31, 077202. | 1.3 | 0 |
| 42 | Selective area growth of InN nanocolumns: Effect of lattice polarity. , 2015, , . | | 0 |
| 43 | E-beam pumped mid-ultraviolet sources based on AlGaN multiple quantum wells grown by MBE. , 2015, , . | | 0 |
| 44 | Fabrication of monolayer-thick InN/InGaN single-quantum-well structures emitting at 1.55Î¼m. , 2015, , . | | 0 |
| 45 | Observing near-infrared/ultraviolet responses within GaN/AlN superlattice for dual-band detection. , 2020, , . | | 0 |
| 46 | Lattice Polarity Manipulation of Quasiâ€vdW Epitaxial GaN Films on Graphene Through Interface Atomic Configuration (Adv. Mater. 5/2022). Advanced Materials, 2022, 34, . | 11.1 | 0 |